

February 2002

LMV712

Low Power, Low Noise, High Output, RRIO Dual Operational Amplifier with Independent Shutdown

General Description

The LMV712 duals are high performance BiCMOS operational amplifiers intended for applications requiring Rail-to-Rail inputs combined with speed and low noise. They offer a bandwidth of 5MHz and a slew rate of 5V/µs and can handle capacitive loads of up to 200pF without oscillation.

The LMV712 offers two independent shutdown pins. This feature allows disabling of each device separately and reduces the supply current to less than 1µA typical. The output voltage rapidly ramps up smoothly with no glitch as the amplifier comes out of the shutdown mode.

The LMV712 with the shutdown feature is offered in space saving 10-Bump micro SMD and 10 pin Leadless Leadframe Package (LLP) packages. It is also offered in 10 lead MSOP package. These packages are designed to meet the demands of small size, low power, and low cost required by cellular phones and similar battery operated portable electronics.

Features

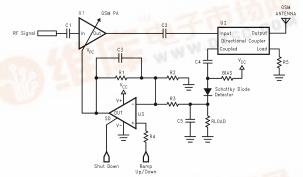
(Typical Unless Otherwise Noted)

- 5 MHz GBP
- Slew rate 5 V/µs
- Low noise 20nV/ √Hz
- Supply current 1.22mA/channel
- V_{OS}< 3mV max.</p>
- Low supply voltage 2.7V to 5V.
- Rail-to-Rail inputs and outputs.
- Unity gain stable.
- Small package: 10-Pin LLP, 10-Pin MSOP and 10-Bump micro SMD
- 1.5µA shutdown I_{CC}
- 2.2µs turn on

Applications

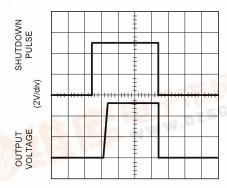
- Power amplifier control loop
- Cellular phones
- Portable equipment
- Wireless LAN
- Radio systems
- Cordless phones

Typical Application Circuit



P.A. Control Loop

Output Waveform vs. Shutdown Pulse



TIME (2µs/div)

10137030



Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

ESD Tolerance (Note 2)

Machine Model 150V
Human Body Model 1.5kV
Differential Input Voltage ±Supply Voltage

Voltage at Input/Output Pin (V^+) +0.4V to (V^-) -0.4V

Supply Voltage (V $^+$ - V $^-$) 5.5V Output Short Circuit V $^+$ (Note 3)

Output Short Circuit V⁻ (Note 3)
Current at Input Pin ±10mA
Current at Output Pin ±50mA

Storage Temp Range -65°C to 150°C

Mounting Temperature

Infrared or Convection (20 235°C

sec)

Junction Temperature T_{JMAX} 150°C (Note 4)

Recommended Operating Conditions (Note 1)

Supply Voltage 2.7V to 5V Temperature Range $-40^{\circ}\text{C} \leq \text{T}_{\text{J}} \leq 85^{\circ}\text{C}$

Thermal Resistance

 10-Pin MSOP
 235°C/W

 10-Pin LLP
 53.4°C/W

 10-Bump micro SMD
 196°C/W

2.7V Electrical Characteristics Unless otherwise specified, all limits guaranteed for V⁺ = 2.7V, V $^-$ = 0V, V_{CM} = 1.35V and T_A = 25°C and R_L > 1M Ω . **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Condition	Min (Note 6)	Typ (Note 5)	Max (Note 6)	Units
V _{OS}	Input Offset Voltage	$V_{CM} = 0.85V$ and $V_{CM} = 1.85V$		0.4	3 3.2	mV
I _B	Input Bias Current			5.5	115 130	рА
CMRR	Common Mode Rejection Ratio	0V ≤ V _{CM} ≤ 2.7V	50 45	75		dB
PSRR	Power Supply Rejection Ratio	$2.7V \le V^{+} \le 5V,$ $V_{CM} = 0.85V$	70 68	90		dB
		$2.7V \le V^{+} \le 5V,$ $V_{CM} = 1.85V$	70 68	90		dB
CMVR	Common Mode Voltage Range	For CMRR ≥ 50dB		-0.3	-0.2	V
			2.9	3		V
I _{SC}	Output Short Circuit Current	Sourcing $V_O = 0V$	15 12	25		mA
		Sinking V _O = 2.7V	25 22	50		mA
Vo	Output Swing	$R_L = 10k\Omega$ to 1.35V	2.62 2.60	2.68		V
				0.01	0.12 0.15	V
		$R_L = 600\Omega$ to 1.35V	2.52 2.50	2.55		V
				0.05	0.23 0.30	V
V _O (SD)	Output Voltage in Shutdown			10	200	mV
I _S	Supply Current per Channel	On Mode		1.22	1.7 1.9	mA
		Shutdown Mode		0.12	1.5 2.0	uA

2.7V Electrical Characteristics Unless otherwise specified, all limits guaranteed for V⁺ = 2.7V, V $^-$ = 0V, V_{CM} = 1.35V and T_A = 25°C and R_L > 1M Ω . **Boldface** limits apply at the temperature extremes. (Continued)

Symbol	Parameter	Condition	Min	Тур	Max	Units
			(Note 6)	(Note 5)	(Note 6)	
A _{VOL}	Large Signal Voltage Gain	Sourcing	80	115		dB
		$R_L = 10k\Omega$	76			
		$V_{\rm O} = 1.35 V$ to 2.3 V				
		Sinking	80	113		dB
		$R_L = 10k\Omega$	76			
		$V_{\rm O} = 0.4 V$ to 1.35 V				
		Sourcing	80	97		dB
		$R_L = 600\Omega$	76			
		$V_{\rm O} = 1.35 V \text{ to } 2.2 V$				
		Sinking	80	100		dB
		$R_L = 600\Omega$	76			
		$V_{\rm O} = 0.5 V$ to 1.35 V				
V_{SD}	Shutdown Pin Voltage Range	On Mode	2.4 to 2.7	2.0 to 2.7		V
		Shutdown Mode	0 to 0.8	0 to 1		V
GBWP	Gain-Bandwidth Product			5		MHz
SR	Slew Rate	(Note 7)		5		V/µs
φ _m	Phase Margin			60		Deg
e _n	Input Referred Voltage Noise	f = 1kHz		20		nV/√Hz
T _{ON}	Turn-On Time from Shutdown			2.2	4	μs
					4.6	
	Turn-On Time from Shutdown		6			μs
	(micro SMD)		8			

5V Electrical Characteristics

Unless otherwise specified, all limits guaranteed for V⁺ =5V, V $^-$ = 0V, V_{CM} = 2.5V and T_A = 25°C and R_L > 1M Ω . **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Condition	Min	Тур	Max	Units
			(Note 6)	(Note 5)	(Note 6)	
Vos	Input Offset Voltage	$V_{CM} = 0.85V$ and		0.4	3	mV
		$V_{CM} = 1.85V$			3.2	
I _B	Input Bias Current			5.5	115	pА
					130	
CMRR	Common Mode Rejection Ratio	$0V \le V_{CM} \le 5V$	50	80		dB
			45			
PSRR	Power Supply Rejection Ratio	$2.7V \le V^+ \le 5V$,	70	90		dB
		$V_{CM} = 0.85V$	68			
		$2.7V \le V^+ \le 5V$,	70	90		dB
		$V_{CM} = 1.85V$	68			
CMVR	Common Mode Voltage Range	For CMRR ≥ 50dB		-0.3	-0.2	V
			5.2	5.3		V
I _{SC}	Output Short Circuit Current	Sourcing	20	35		mA
		$V_O = 0V$	18			
		Sinking	25	50		mA
		V _O = 5V	21			

5V Electrical Characteristics (Continued)

Unless otherwise specified, all limits guaranteed for V⁺ =5V, V $^-$ = 0V, V_{CM} = 2.5V and T_A = 25°C and R_L > 1M Ω . **Boldface** limits apply at the temperature extremes.

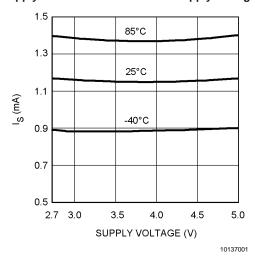
Symbol	Parameter	Condition	Min	Тур	Max	Units
			(Note 6)	(Note 5)	(Note 6)	
V_{O}	Output Swing	$R_L = 10k\Omega$ to 2.5V	4.92	4.98		V
			4.90			
				0.01	0.12	V
					0.15	
		$R_L = 600\Omega$ to 2.5V	4.82	4.85		V
			4.80			
				0.05	0.23	V
					0.30	
V _O (SD)	Output Voltage in Shutdown			10	200	mV
Is	Supply Current per Channel	On Mode		1.17	1.7	mA
					1.9	
		Shutdown Mode		0.12	1.5	uA
					2.0	
A_{VOL}	Large Signal Voltage Gain	Sourcing	80	130		dB
		$R_L = 10k\Omega$	76			
		$V_{O} = 2.5V \text{ to } 4.6V$				
		Sinking	80	130		dB
		$R_L = 10k\Omega$	76			
		$V_{\rm O} = 0.4 V \text{ to } 2.5 V$				
		Sourcing	80	110		dB
		$R_L = 600\Omega$	76			
		$V_{\rm O} = 2.5 \text{V to } 4.6 \text{V}$				
		Sinking	80	107		dB
		$R_L = 600\Omega$	76			
		$V_{\rm O} = 0.4 V \text{ to } 2.5 V$				
V_{SD}	Shutdown Pin Voltage Range	On Mode	4.5 to 5	3.5 to 5		V
		Shutdown Mode	0 to 0.8	0 to 1.5		V
GBWP	Gain-Bandwidth Product			5		MHz
SR	Slew Rate	(Note 7)		5		V/µs
φ _m	Phase Margin			60		Deg
e _n	Input Referred Voltage Noise	f = 1kHz		20		nV/ √Hz
T _{ON}	Turn-On Time for Shutdown			1.6	4	μs
					4.6	
	Turn-On Time for Shutdown		6			μs
	(micro SMD)		8			

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not guaranteed. For guaranteed specifications and the test conditions, see the Electrical Characteristics.

- **Note 2:** Human body model: $1.5k\Omega$ in series with 100pF. Machine model, 0Ω in series with 100pF.
- Note 3: Shorting circuit output to either V⁺ or V⁻ will adversely affect reliability.
- Note 4: The maximum power dissipation is a function of $T_{J(MAX)}$, θ_{JA} and T_A . The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(MAX)} T_A)/\theta_{JA}$. All numbers apply for packages soldered directly into a PC board.
- Note 5: Typical values represent the most likely parametric norm.
- Note 6: All limits are guaranteed by testing or statistical analysis.
- Note 7: Number specified is the slower of the positive and negative slew rates.

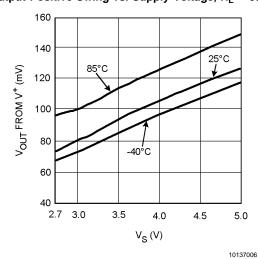
Typical Performance Characteristics Unless otherwise specified, $V_S = +5V$, single suppy, $T_A = 25^{\circ}C$.

Supply Current Per Channel vs. Supply Voltage

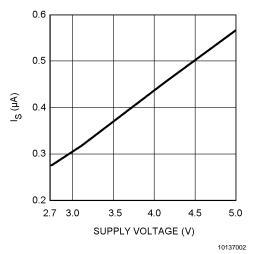


V_{OS} vs. V_{CM} -200 -40°C -4

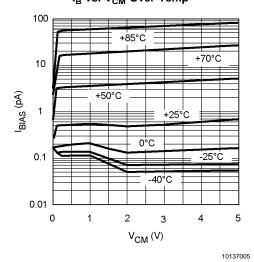
Output Positive Swing vs. Supply Voltage, $R_L = 600\Omega$



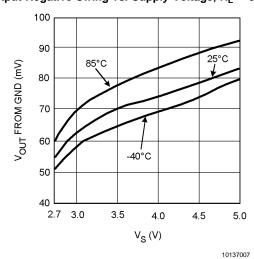
Supply Current vs. Supply Voltage (Shutdown)



 ${\rm I_B}$ vs. ${\rm V_{CM}}$ Over Temp

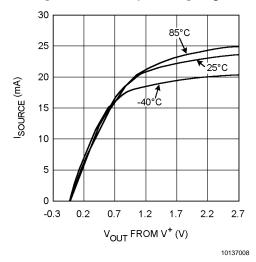


Output Negative Swing vs. Supply Voltage, $R_L = 600\Omega$

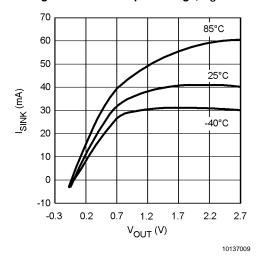


Typical Performance Characteristics Unless otherwise specified, $V_S = +5V$, single suppy, $T_A = 25^{\circ}C$. (Continued)

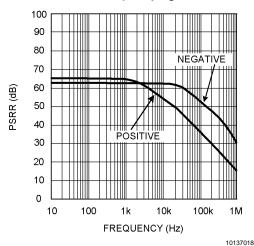
Sourcing Current vs. Output Voltage, $V_S = 2.7V$



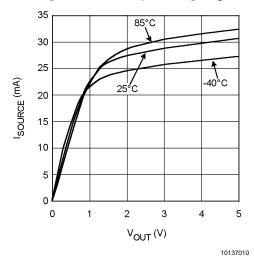
Sinking Current vs. Output Voltage, $V_S = 2.7V$



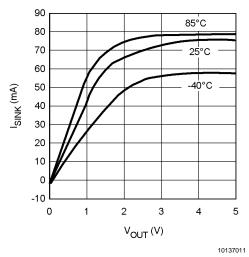
PSRR vs. Frequency $V_S = 2.7V$



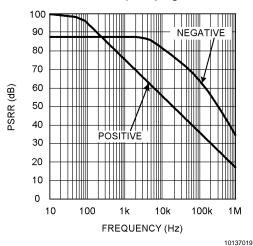
Sourcing Current vs. Output Voltage, $V_S = 5V$



Sinking Current vs. Output Voltage, $V_S = 5V$

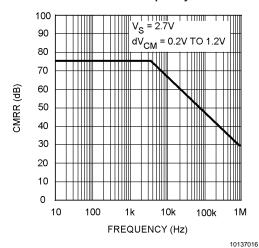


PSRR vs. Frequency $V_S = 5V$

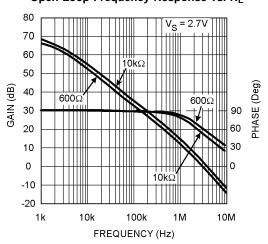


Typical Performance Characteristics Unless otherwise specified, $V_S = +5V$, single suppy, $T_A = 25^{\circ}C$. (Continued)

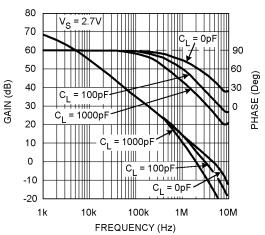




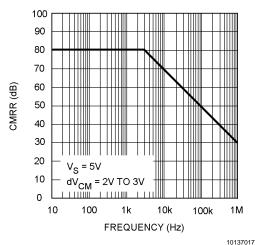
Open Loop Frequency Response vs. R_L



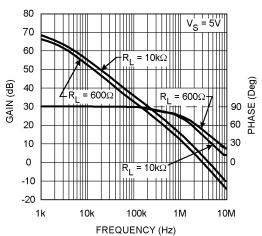
Open Loop Frequency Response vs. C_L



CMRR vs. Frequency

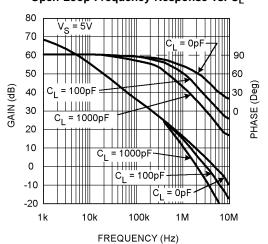


Open Loop Frequency Response vs. R_L



10137014

Open Loop Frequency Response vs. C_L



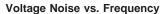
10137015

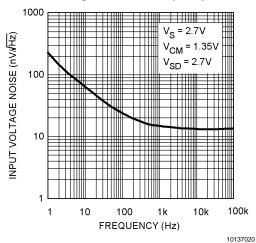
10137012

10137013

Typical Performance Characteristics Unless otherwise specified, $V_S = +5V$, single suppy, $T_A = -5V$ 25°C. (Continued)

1000





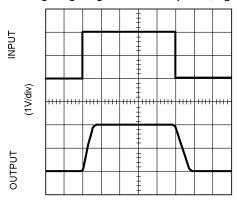
Voltage Noise vs. Frequency

INPUT VOLTAGE NOISE (nV//Hz) 100

10137021

100k

Non-Inverting Large Signal Pulse Response, $V_S = 2.7V$

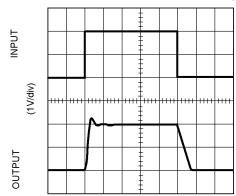


TIME (500ns/div)

10137022

Non-Inverting Large Signal Pulse Response, V_S = 5V

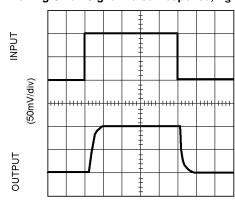
100 FREQUENCY (Hz)



TIME (500ns/div)

10137024

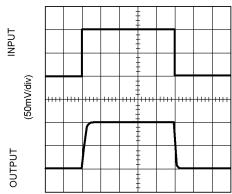
Non-Inverting Small Signal Pulse Response, $V_S = 2.7V$



TIME (500ns/div)

10137023

Non-Inverting Small Signal Pulse Response, $V_S = 5V$

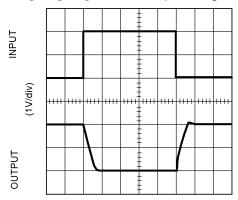


TIME (500ns/div)

10137025

Typical Performance Characteristics Unless otherwise specified, $V_S = +5V$, single suppy, $T_A = 25^{\circ}C$. (Continued)

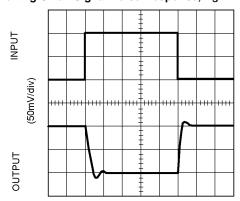
Inverting Large Signal Pulse Response, $V_S = 2.7V$



TIME (500ns/div)

10137026

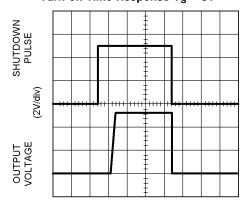
Inverting Small Signal Pulse Response, $V_S = 2.7V$



TIME (500ns/div)

10137027

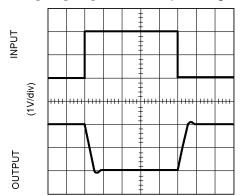
Turn on Time Response $V_S = 5V$



TIME (2µs/div)

10137030

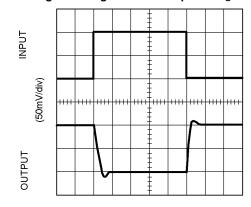
Inverting Large Signal Pulse Response, $V_S = 5V$



TIME (500ns/div)

1013702

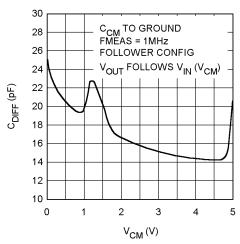
Inverting Small Signal Pulse Response V_S = 5V



TIME (500ns/div)

10137029

Input Common Mode Capacitance vs. $V_{CM} V_S = 5V$



10137004

Application Information

Theory of Operation

The LMV712 dual op amp is derived from the LMV711 single op amp. *Figure 1* contains a simplified schematic of one channel of the LMV712.

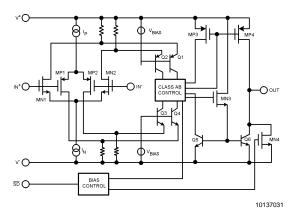


FIGURE 1.

Rail-to-Rail input is achieved by using in parallel, one NMOS differential pair (MN1 and MN2) and one PMOS differential pair (MP1 and MP2). When the common mode input voltage (V_{CM}) is near V⁺, the NMOS pair is on and the PMOS pair is off. When V_{CM} is near V⁻, the NMOS pair is off and the PMOS pair is on. When V_{CM} is between V⁺ and V⁻, internal logic decides how much current each differential pair will get. This special logic ensures stable and low distortion amplifier operation within the entire common mode voltage range.

Because both input stages have their own offset voltage (V_{OS}) characteristic, the offset voltage of the LMV712 becomes a function of V_{CM} . V_{OS} has a crossover point at 1.4V above V^- . Refer to the ' V_{OS} vs. V_{CM} ' curve in the Typical Performance Characteristics section. Caution should be taken in situations where input signal amplitude is comparable to V_{OS} value and/or the design requires high accuracy. In these situations, it is necessary for the input signal to avoid the crossover point.

The current coming out of the input differential pairs gets mirrored through two folded cascode stages (Q1, Q2, Q3, Q4) into the 'class AB control' block. This circuitry generates voltage gain, defines the op amp's dominant pole and limits the maximum current flowing at the output stage. MN3 introduces a voltage level shift and acts as a high impedance to low impedance buffer.

The output stage is composed of a PMOS and a NPN transistor in a common source/emitter configuration, delivering a rail-to-rail output excursion.

The MN4 transistor ensures that the LMV712 output remains near V⁻ when the amplifier is in shutdown mode.

Shutdown Pin

The LMV712 offers independent shutdown pins for the dual amplifiers. When the shutdown pin is tied low, the respective amplifier shuts down and the supply current is reduced to less than 1 μ A. In shutdown mode, the amplifier's output level stays at V⁻. In a 2.7V operation, when a voltage between 1.5V to 2.7V is applied to the shutdown pin, the amplifier is enabled. As the amplifier is coming out of the shutdown mode, the output waveform ramps up without any glitch. This is demonstrated in *Figure 2*.

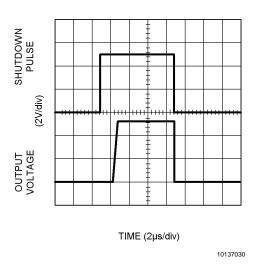


FIGURE 2.

A glitch-free output waveform is highly desirable in many applications, one of which is power amplifier control loops. In this application, the LMV712 is used to drive the power amplifier's power control. If the LMV712 did not have a smooth output ramp during turn on, it would directly cause the power amplifier to produce a glitch at its output. This adversely affects the performance of the system.

To enable the amplifier, the shutdown pin must be pulled high. It should not be left floating in the event that any leakage current may inadvertently turn off the amplifier.

Printed Circuit Board Consideration

To properly bypass the power supply, several locations on a printed circuit board need to be considered. A $6.8\mu F$ or greater tantalum capacitor should be placed at the point where the power supply for the amplifier is introduced onto the board. Another $0.1\mu F$ ceramic capacitor should be placed as close as possible to the power supply pin of the amplifier. If the amplifier is operated in a single power supply, only the V+ pin needs to be bypassed with a $0.1\mu F$ capacitor. If the amplifier is operated in a dual power supply, both V+ and V- pins need to be bypassed.

It is good practice to use a ground plane on a printed circuit board to provide all components with a low inductive ground connection.

Surface mount components in 0805 size or smaller are recommended in the LMV712 application circuits. Designers can take advantage of the micro SMD, MSOP and LLP miniature sizes to condense board layout in order to save space and reduce stray capacitance.

Capacitive Load Tolerance

The LMV712 can directly drive 200pF in unity-gain without oscillation. The unity-gain follower is the most sensitive configuration to capacitive loading. Direct capacitive loading reduces the phase margin of amplifiers. The combination of the amplifier's output impedance and the capacitive load induces phase lag. This results in either an under-damped pulse response or oscillation. To drive a heavier capacitive load, *Figure 3* can be used.

Application Information (Continued)

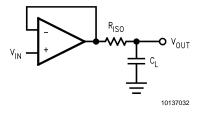


FIGURE 3.

In Figure 3, the isolation resistor $R_{\rm ISO}$ and the load capacitor $C_{\rm L}$ form a pole to increase stability by adding more phase margin to the overall system. The desired performance depends on the value of $R_{\rm ISO}$. The bigger the $R_{\rm ISO}$ resistor value, the more stable $V_{\rm OUT}$ will be. But the DC accuracy is degraded when the $R_{\rm ISO}$ gets bigger. If there were a load resistor in Figure 3, the output voltage would be divided by $R_{\rm ISO}$ and the load resistor.

The circuit in *Figure 4* is an improvement to the one in *Figure 3* because it provides DC accuracy as well as AC stability. In this circuit, R_{F} provides the DC accuracy by using feed-forward techniques to connect V_{IN} to R_{L} . C_{F} and R_{ISO} serve to counteract the loss of phase margin by feeding the high frequency component of the output signal back to the amplifier's inverting input, thereby preserving phase margin

in the overall feedback loop. Increased capacitive drive is possible by increasing the value of C_{F} . This in turn will slow down the pulse response.

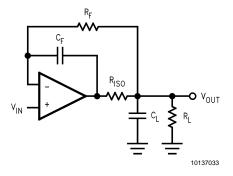


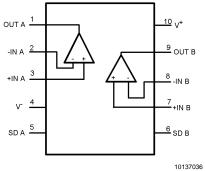
FIGURE 4.

Latchup

CMOS devices tend to be susceptible to latchup due to their internal parasitic SCR (silicon controlled rectifier) effects. The input and output pins look similar to the gate of the SCR. There is a minimum current required to trigger the SCR gate lead. The LMV712 is designed to withstand 150mA surge current on all the pins. Some resistive method should be used to isolate any capacitance from supplying excess current to the pins. In addition, like an SCR, there is a minimum holding current for any latchup mode. Limiting current to the supply pins will also inhibit latchup susceptibility.

Connection Diagrams

10-Pin MSOP



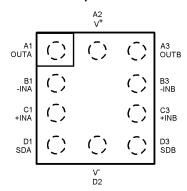
Top View

10-Pin LLP OUT A 1 10 V[†] -IN A 2 9 OUT B +IN A 3 -IN B V 4 7 +IN B SD A 5 6 SD B

Top View

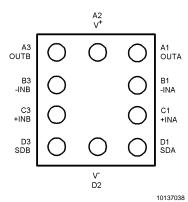
10137035

10-Bump micro SMD



Top View

10137037

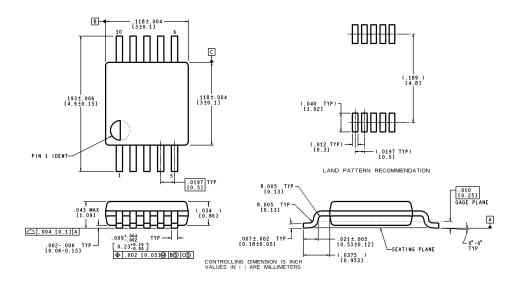


Bottom View

Ordering Information

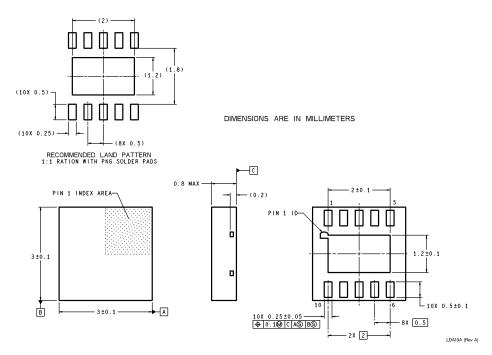
Package	Part Number	Package Marking	Transport Media	NSC Drawing
10-Pin MSOP	MSOP LMV712MM A61 1k Units Tape and Reel		1k Units Tape and Reel	MUB10A
	LMV712MMX		3.5k Units Tape and Reel	
10-Pin LLP LMV712LD		A62	1k Units Tape and Reel	LDA10A
	LMV712LDX		3.5k Units Tape and Reel	
10-Bump micro SMD	LMV712BL	A76A	250 Units Tape and Reel	BLP10AAB
	LMV712BLX		3k Units Tape and Reel	

Physical Dimensions inches (millimeters) unless otherwise noted



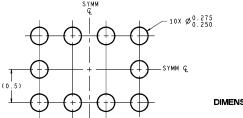
MUB10A (Rev A)

10-Pin MSOP **NS Package Number MUB10A**

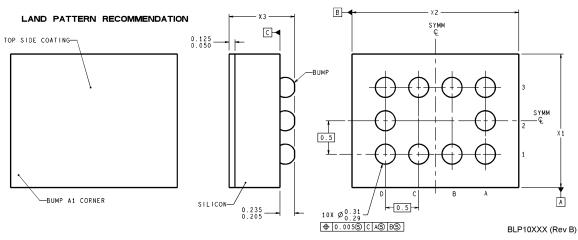


10-Pin LLP **NS Package Number LDA10A**

Physical Dimensions inches (millimeters) unless otherwise noted (Continued)



DIMENSIONS ARE IN MILLIMETERS



NOTES: UNLESS OTHERWISE SPECIFIED

- 1. EPOXY COATING
- 2. Sn/37Pb EUTECTIC BUMP
- 3. RECOMMEND NON-SOLDER MASK DEFINED LANDING PAD.
- 4. PIN A1 IS ESTABLISHED BY LOWER LEFT CORNER WITH RESPECT TO TEXT ORIENTATION. REMAINING PINS ARE NUMBERED COUNTER CLOCKWISE.
- 5. XXX IN DRAWING NUMBER REPRESENTS PACKAGE SIZE VARIATION WHERE X1 IS PACKAGE WIDTH, X2 IS PACKAGE LENGTH AND X3 IS PACKAGE HEIGHT.
- 6. REFERENCE JEDEC REGISTRATION MO-211, VARIATION BC.

LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT AND GENERAL COUNSEL OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
- A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.



www.national.com

Europe Fax:

Fax: +49 (0) 180-530 85 86 Email: europe.support@nsc.com Deutsch Tel: +49 (0) 69 9508 6208 English Tel: +44 (0) 870 24 0 2171 Français Tel: +33 (0) 1 41 91 8790

National Semiconductor

National Semiconductor Asia Pacific Customer Response Group Tel: 65-2544466 Fax: 65-2504466 Email: ap.support@nsc.com National Semiconductor Japan Ltd. Tel: 81-3-5639-7560 Fax: 81-3-5639-7507